TELEFUNKEN Semiconductors

Optocoupler with Phototransistor Output

Description

The CNY21N consists of a phototransistor optically coupled to a gallium arsenide infrared emitting diode in a 4 lead plastic dual inline packages.

The single components are mounted on one leadframe in opposite position, providing a fixed distance between input and output for highest safety requirements of > 3 mm.

Application

Circuits for safe protective separation against electrical shock according to safety class II. (reinforced isolation):

- for application class I IV at main voltage $\leq 300 \text{ V}$
- for application class I IV at main voltage $\leq 600 V$:
- for application class I III at main voltage ≤ 1000 V according, to VDE 0884, table 2, suitable for:

Switch mode power supplies, computer peripheral interface, microprocessor system interface, line receiver.







These couplers perform safety functions according to following equipment standards:

• VDE 0884

Optocoupler providing protective separation

VDE 0804

Telecommunication apparatus and data processing

• VDE 0805/IEC 950/EN 60950

Office machines (applied for reinforced isolation for main voltage $\leq 400 \text{ V}_{RMS}$)

• VDE 0860/IEC 65

Safety for mains operated electronic and related apparatus for household

• VDE 0700/IEC 335

Household equipment

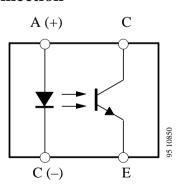
• VDE 0160

Electronic equipment for electrical power installation

VDE 0750/IEC 601

Medical equipment

Pin Connection



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Features

According to VDE 0884

- Rated impulse voltage (transient overvoltage)
 V_{IOTM} = 8 kV peak
- Isolation test voltage (partial discharge test voltage)
 V_{pd} = 2.8 kV peak
- Rated isolation voltage (RMS includes DC)
 V_{IOWM} = 1000 V_{RMS} (1450 V peak)
- Rated recurring peak voltage (repetitive)
 V_{IORM} = 1000 V_{RMS}
- Creeping current resistance according to VDE 0303/IEC 112
 Comparative Tracking Index: CTI = 275

- Thickness through insulation > 3 mm
- Isolation materials according to UL 94
- Pollution degree 2 (DIN/VDE 0110)
- Climatic classification 55/085/21 (IEC 68 part 1)
- Further approvals: BS 415, BS 7002, SETI: IEC 950, UL 1577: File no: E 76222
- Special construction: therefore extra low coupling capacity typical 0.3 pF, high Common Mode Rejection
- Low temperature coefficient of CTR
- Current Transfer Ratio CTR: 60% typical

Absolute Maximum Ratings

Input (Emitter)

Parameters	Test Conditions	Symbol	Value	Unit
Reverse voltage		V_{R}	5	V
Forward current		I_{F}	50	mA
Forward surge current	$t_p \le 10 \ \mu s$	I _{FSM}	1.5	A
Power dissipation	$T_{amb} \le 25^{\circ}C$	P _{tot}	120	mW
Junction temperature		Ti	100	°C

Output (Detector)

Parameters	Test Conditions	Symbol	Value	Unit
Collector emitter voltage		V_{CEO}	32	V
Emitter collector voltage		V_{ECO}	5	V
Collector current		I_{C}	50	mA
Collector peak current	$t_p/T = 0.5, t_p \le 10 \text{ ms}$	I_{CM}	100	mA
Power dissipation	$T_{amb} \le 25^{\circ}C$	P _{tot}	130	mW
Junction temperature		T _i	100	°C

Coupler

Parameters	Test Conditions	Symbol	Value	Unit
AC isolation test voltage (RMS)		V _{IO}	8.2	kV
Total power dissipation	$T_{amb} \le 25^{\circ}C$	P _{tot}	250	mW
Ambient temperature range		T _{amb}	-55 to +85	°C
Storage temperature range		T _{stg}	-55 to +100	°C
Soldering temperature	2 mm from case t ≤ 10 s	T _{sd}	260	°C

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Maximum Safety Ratings $^{1)}$ (according to VDE 0884)

Input (Emitter)

Parameters	Parameters Test Conditions		Value	Unit
Forward current		I_{si}	120	mA

Output (Detector)

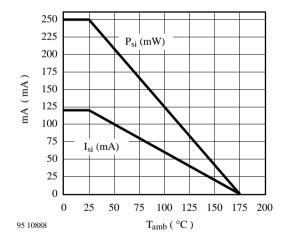
Parameters	Test Conditions	Symbol	Value	Unit
Power dissipation	$T_{amb} \le 25^{\circ}C$	P_{si}	250	mW

Coupler

Parameters	Test Conditions	Symbol	Value	Unit
Rated impulse voltage		V _{IOTM}	8	kV
Safety temperature		T _{si}	180	°C

This device is used for protective separation against electrical shock only within the maximum safety ratings. This must be ensured by protective circuits in the applications.

Derating Diagram



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CNY21N

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Electrical Characteristics

 $T_{amb} = 25^{\circ}C$

Input (Emitter)

Parameters	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
Forward voltage	$I_F = 50 \text{ mA}$	V_{F}		1.25	1.6	V
Breakdown voltage	$I_R = 100 \mu A$	$V_{(BR)}$	5			V
Junction capacitance	$V_R = 0$, $f = 1$ MHz	C _i		50	·	pF

Output (Detector)

Parameters	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
Collector emitter breakdown voltage	$I_C = 1 \text{ mA}$	V _{(BR)CEO}	32			V
Emitter collector breakdown voltage	$I_E = 100 \mu A$	V _{(BR)ECO}	5			V
Collector emitter cut-off current	$V_{CE} = 20 \text{ V}, I_f = 0$	I_{CEO}			200	nA

Coupler

Parameters	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
AC isolation test voltage (RMS)	f = 50 Hz, t = 1 s	V _{IO}	8.2			kV
Collector emitter saturation voltage	$I_F = 10 \text{ mA}, I_C = 1 \text{ mA}$	V _{CEsat}			0.3	V
Cut-off frequency	$V_{CE} = 5 \text{ V}, I_F = 5 \text{ mA},$ $R_L = 100 \Omega$	f_c		170		kHZ
Coupling capacitance	f = 1 MHz	C_k		0.3		pF
$I_{\rm C}/I_{\rm F}$	$I_F = 10 \text{ mA}, V_{CE} = 5 \text{ V}$	CTR	0.25	0.6		

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Switching Characteristics (Typical Values)

 $V_S = 5 V$

Type		$R_L = 100 \text{ k}\Omega$, see figure 1							$R_L = 1 \text{ k}\Omega$, see fig. 2		
	t _d [μs]	t _r [µs]	ton[µs]	t _s [μs]	t _f [µs]	t _{off} [µs]	I _C [mA]	ton[µs]	t _{off} [µs]	I _F [mA]	
CNY21N	2.6	2.4	5.0	0.3	2.7	3.0	5	11	13.5	20	

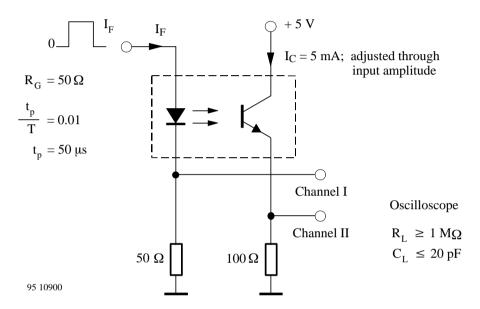


Figure 1. Test circuit, non-saturated operation

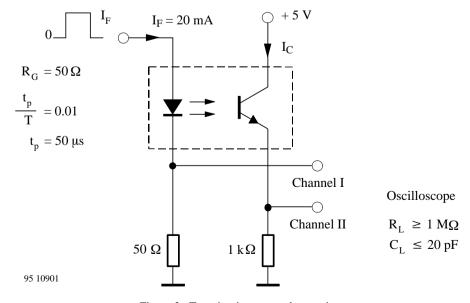


Figure 2. Test circuit, saturated operation

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Insulation Rated Parameters (according to VDE 0884)

Paran	neters	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
Doutiel dischause	Routine test	100%, $t_{test} = 1 \text{ s}$	V_{pd}	2.8			kV
Partial discharge	Lot test	$t_{Tr} = 10 \text{ s},$	V _{IOTM}	8			kV
test voltage	(sample test)	$t_{test} = 60 \text{ s}$ see figure 3	V _{pd}	2.2			kV
$V_{IO} = 5$		$V_{IO} = 500 \text{ V}$	R_{IO}	10 ¹²			Ω
		$V_{IO} = 500 \text{ V},$ $T_{amb} = 100^{\circ}\text{C}$	R_{IO}	10 ¹¹			Ω
insulation	resistance	$V_{IO} = 500 \text{ V},$ $T_{amb} = 180^{\circ}\text{C}$	R_{IO}	10 ⁹			Ω
		(only construction test)					

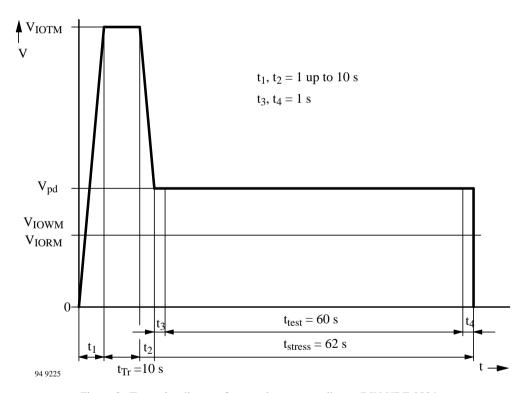


Figure 3. Test pulse diagram for sample test according to DIN VDE 0884

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Ozone Depleting Substances Policy Statement

It is the policy of TEMIC TELEFUNKEN microelectronic GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

TEMIC TELEFUNKEN microelectronic GmbH semiconductor division has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

TEMIC can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use TEMIC products for any unintended or unauthorized application, the buyer shall indemnify TEMIC against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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